



Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	160mΩ @ V_{GS} = -4.5V	-2.4A
-20V	210mΩ @ V _{GS} = -2.5V	-2.1A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Backlighting
- **Power Management Functions**
- **DC-DC Converters**
- Motor Control

ESD protected Gate





Top View

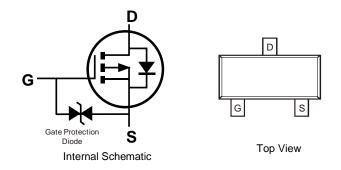
P-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **ESD** Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23 •
- Case Material: Molded Plastic, "Green" Molding Compound. . UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish —Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)



Ordering Information (Note 4)

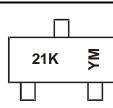
Part Number	Case	Packaging
DMG2301LK-7	SOT23	3,000/Tape & Reel
DMG2301LK-13	SOT23	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimonv compounds.

For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



21K = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	2016		2017	2018		2019	2020		2021	2022		2023
Code	D		E	F		G	Н			J		K
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	S	2	4	5	6	7	0	0	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	-20	V
Gate-Source Voltage		V _{GSS}	±12	V
Continuous Drain Current (Note 6) $V_{GS} = -4.5V$ State $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		ID	-2.4 -1.9	А
Maximum Continuous Body Diode Forward Curre	nt (Note 6)	ls	-1.12	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	1%)	I _{DM}	-8	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.84	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	150	°C/W
Total Power Dissipation (Note 6)		PD	1.40	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	91	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified)

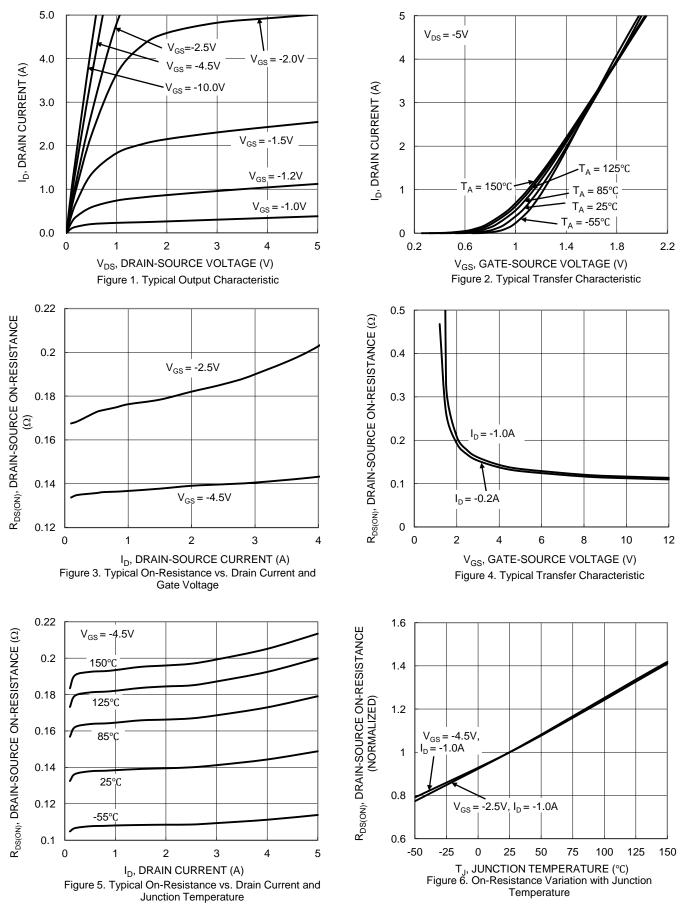
Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	• • • • • • •		• 76		•	
Drain-Source Breakdown Voltage	BV _{DSS}	-20			V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current ($T_J = +25^{\circ}C$)	I _{DSS}	_		-10	μA	$V_{DS} = -16V, V_{GS} = 0V$
Gate-Source Leakage	IGSS			±10	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						÷
Gate Threshold Voltage	V _{GS(TH)}	-0.3	-0.6	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250A$
			136	160		$V_{GS} = -4.5V, I_D = -1.0A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	183	210	mΩ	$V_{GS} = -2.5V, I_D = -1.0A$
			229	298		$V_{GS} = -1.8V, I_D = -0.2A$
Diode Forward Voltage	V _{SD}	_	-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -1.0A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		156		pF	
Output Capacitance	Coss		36		pF	$V_{DS} = -6V, V_{GS} = 0V$ - f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		28		pF	1 = 1.00012
Gate Resistance	Rg		41		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg		1.6		nC	
Total Gate Charge (V _{GS} = -10V)	Qg	_	3.4		nC	$V_{DS} = -6V,$
Gate-Source Charge	Q _{gs}	_	0.3		nC	I _D = -2.2A
Gate-Drain Charge	Q _{gd}	_	0.4		nC	
Turn-On Delay Time	t _{D(ON)}	_	3.2		ns	
Turn-On Rise Time	t _R	_	7.4		ns	$V_{DS} = -6V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t _{D(OFF)}		11.0		ns	$R_{GEN} = 6 \Omega$, $I_D = -1A$
Turn-Off Fall Time	t _F		10.5		ns	7
Reverse Recovery Time	t _{RR}	_	6.5		ns	
Reverse Recovery Charge	Q _{RR}		0.8	—	nC	I _F = -1.0A, di/dt = 100A/µs

5. Device mounted on FR-4 PCB, with minimum recommended pad layout. Notes:

Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

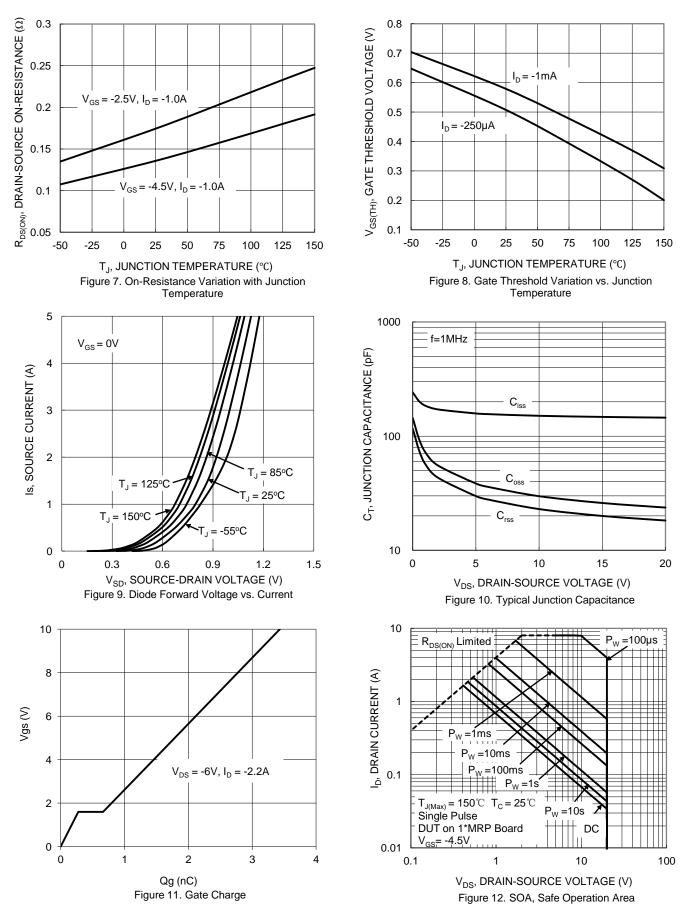


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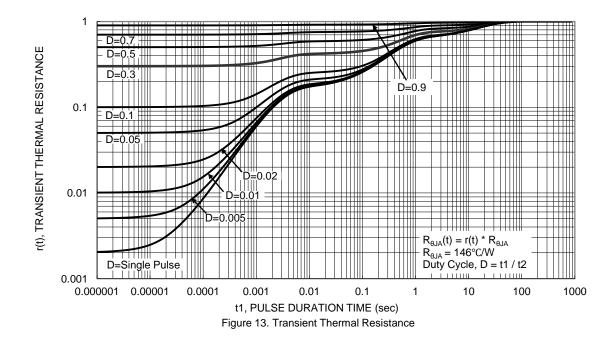


DMG2301LK



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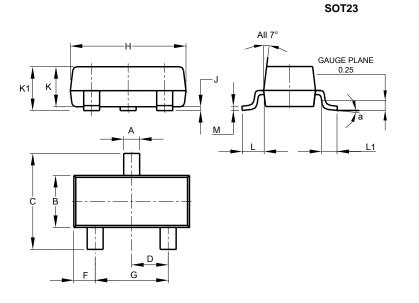






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

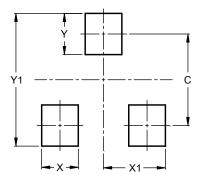


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
κ	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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